

Dual-Rail Ultra-Low Dropout 1A LDO

General Description

The ET5A2ADJZB is CMOS-based low-dropout, low-power linear regulators, offering 1000mA with NMOS pass transistor and a separate bias supply voltage (V_{BIAS}). The device provides very stable, accurate output voltage with low noise, high ripple rejection and low supply current suitable for space constrained, noise sensitive application.

ET5A2ADJZB consists of an accurate voltage-reference block, an error amplifier, a thermal shutdown circuit, and a current limit circuit.

Features

- Wide V_{IN} input voltage range from V_{OUT} to 5.5V
- Wide V_{BIAS} voltage range from 3.0V to 5.5V
- Output voltage range from 0.5V to 3.0V adjustable
- Very low V_{BIAS} input current of typical 35 μ A
- Ultra low dropout is typical 40mV at 1000mA load
- Built-in over-current protection and thermal shutdown circuit
- Built-in auto-discharging circuit (optional)
- Built-in under voltage lock-out
- Package information:

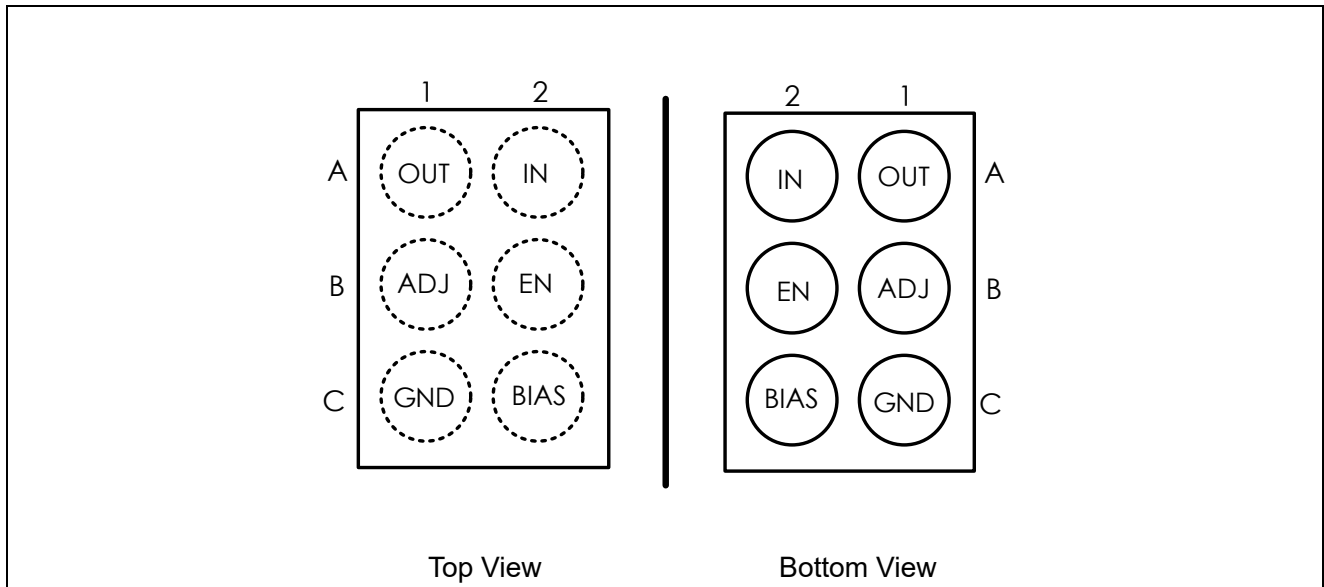
Part No.	Package	MSL
ET5A2ADJZB	WLCSP6 (1.14mm×0.74mm,0.4 pitch)	Level 1

Applications

- Constant-voltage power supply for battery-powered device
- Constant-voltage power supply for smartphones, tablets
- Constant-voltage power supply for cameras, DVRs, STB and camcorders

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Pin Configuration

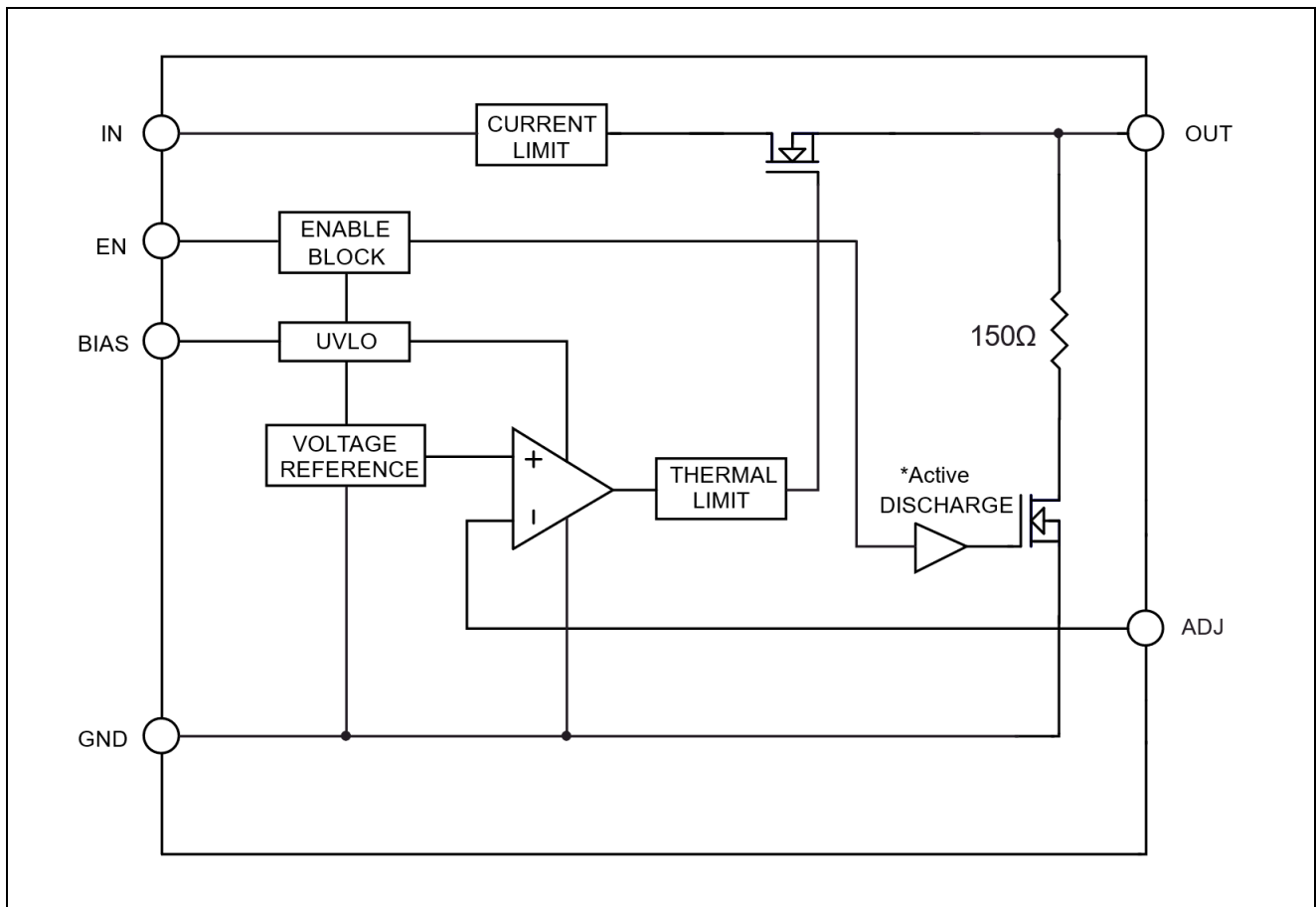


Pin Function

Pin Name	Symbol	Pin Description
A1	OUT	The power output of the device. A 22 μ F (typ.) ceramic capacitor is recommended at this pin.
A2	IN	Input voltage Pin. Large bulk capacitance should be placed closely to this pin. A 1 μ F (typ.) ceramic capacitor is recommended at this pin.
B1	ADJ	Adjustable Regulator Feedback Input. Connect to output voltage resistor divider central node.
B2	EN	Enable Input.
C1	GND	Ground pin.
C2	BIAS	Input voltage for controlling circuit.

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Block Diagram



Functional Description

The ET5A2ADJZB dual-rail very low dropout voltage regulator is using NMOS pass transistor for output voltage regulation from V_{IN} voltage. All the low current internal control circuitry is powered from the V_{BIAS} voltage.

The use of an NMOS pass transistor offers several advantages in applications. Unlike PMOS topology devices, the output capacitor has reduced impact on loop stability. V_{IN} to V_{OUT} operating voltage difference can be very low compared with standard PMOS regulators in very low V_{IN} applications.

The ET5A2ADJZB offers smooth start-up.

Input and output Capacitor

The device is designed to be stable for ceramic output capacitors with 22 μ F capacitance. The device is also stable with multiple capacitors in parallel. In applications where no low input supplies impedance available (PCB inductance in V_{IN} and/or V_{BIAS} inputs as example), the recommended C_{IN} = 10 μ F and C_{BIAS} = 1 μ F or greater.

Enable Pin Operation

The ET5A2ADJZB is turned on by setting the EN pin to “H”. The threshold limits are covered in the electrical

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characteristics table in this datasheet. When the EN pin is not used, connect the EN pin with V_{BIAS} to keep the LDO in operating mode.

Current Limit Protection

When output current of V_{OUT} pin is higher than current limit threshold or the V_{OUT} pin is direct short to GND, the current limit protection will be triggered and clamp the output current at a predesigned level to prevent over-current and thermal damage.

Thermal Shutdown Protection

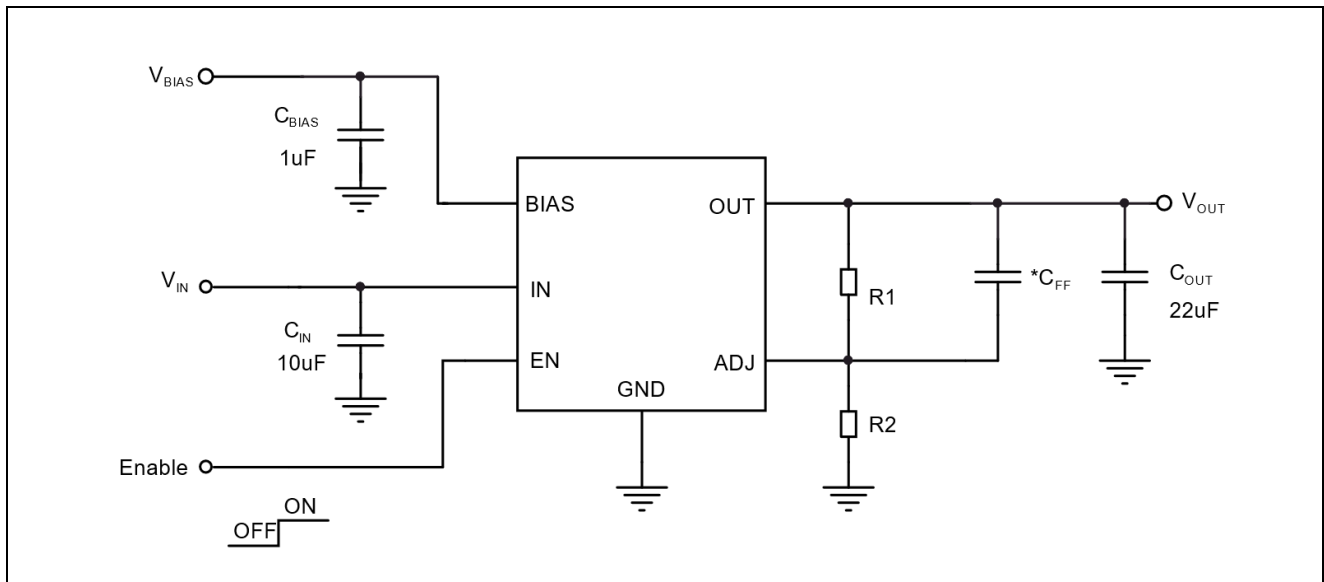
Thermal protection disables the output when the junction temperature rises to approximately $+160^{\circ}\text{C}$, allowing the device to cool down. When the junction temperature reduces to approximately $+140^{\circ}\text{C}$ the output circuit is enabled again. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits the heat dissipation of the regulator, protecting it from damage due to overheating.

Auto Discharging

When the EN pin set to “L”, the output circuit will be disable immediately, and the Auto-Discharging circuit will be turned on to discharge the electric charge on output capacitor, and decrease the voltage of V_{OUT} in very short time.

Output Voltage Adjust

The required output voltage of Adjustable devices can be adjusted from V_{REF} to 3.0 V using two external resistors. Typical application schematics is shown blow.



$$V_{OUT} = V_{REF} \times (1 + R1/R2)$$

Typical value of V_{REF} (ADJ Pin) is 0.5V. It is recommended to keep the total serial resistance of resistors ($R1 + R2$) no greater than 100k Ω .

The output voltage needs to take into account the error caused by the resistance accuracy.

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Absolute Maximum Ratings

Item	Rating	Unit
Input Voltage(IN Pin)	-0.3 to 6.0	V
Input Voltage (BIAS Pin)	-0.3 to 6.0	V
Input Voltage (EN Pin)	-0.3 to 6.0	V
Input Voltage (FB Pin)	-0.3 to 6.0	V
Output Voltage(OUT Pin)	-0.3 to 6.0	V
Maximum Load Current	1000	mA
Maximum Power Consumption	1150	mW
Storage Temperature Range	-65 to 150	°C
Lead Temperature (Soldering, 10 sec)	260	°C
Operating Junction Temperature	-40 to +150	°C
Thermal Resistance, Junction-to-Air	87	°C/W

Recommended Operating Conditions

Symbol	Item	Rating	Unit
V _{IN}	IN Input Voltage	V _{OUT} + V _{DROP} to 5.5	V
V _{BIAS}	BIAS Input Voltage	3 to 5.5 & V _{BIAS} >V _{OUT} +1.6V	V
I _{OUT}	Output Current	0 to 1000	mA
T _A	Operating Ambient Temperature	-40 to 85	°C
C _{IN}	Effective Input Ceramic Capacitor Value	4.7 to 22	μF
C _{BIAS}	Effective Input Ceramic Capacitor Value	0.22 to 4.7	μF
C _{OUT}	Effective Output Ceramic Capacitor Value	10 to 33	μF
ESR	Input and Output Capacitor Equivalent Series Resistance	5 to 100	mΩ

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Electrical Characteristics

(Unless otherwise noted , $V_{IN}=V_{OUT}+0.3V$, $V_{BIAS}= 3.0V$, $I_{OUT}=10mA$, $C_{IN}=10\mu F$, $C_{OUT}=22\mu F$, $C_{BIAS}=1\mu F$,
 $T_A = -40^{\circ}C \sim 125^{\circ}C$. Typical values are at. $T_A = 25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Voltage Range	$V_{IN}^{(1)}$	$V_{IN}>V_{OUT}$	$V_{OUT}+V_{DROP}$		5.5	V
V_{BIAS} Voltage Range	V_{BIAS}	$V_{BIAS}>3.0$, $V_{BIAS}> V_{OUT}+1.6$	3.0		5.5	V
Under-voltage lock-out	V_{UVLO}	V_{BIAS} Rising	1.25	1.6	1.95	V
	V_{UVLO_H}	Hysteresis	0.05	0.2	0.35	V
V_{BIAS} Current	I_{Q_ON}	Active mode: $V_{EN}=high$		35	60	μA
	I_{Q_OFF}	$V_{EN}=0V$		0.2	1	μA
FB Voltage	V_{FB}	$T_A=25^{\circ}C$	0.495		0.505	V
Output Voltage	V_{OUT}		0.5		3.0	V
Dropout Voltage	$V_{DROP}^{(2)}$	$I_{OUT}=500mA$, $V_{OUT}=1.05V$	10	20	35	mV
		$I_{OUT}=1000mA$, $V_{OUT}=1.05V$	20	40	70	
Current Limit	I_{LIM}	$T_A=25^{\circ}C$	1.5	2	2.6	A
Load Regulation	Reg_{LOAD}	$1mA \leq I_{OUT} \leq 1000mA$		2	10	mV
V_{IN} Line Regulation	Reg_{LINE}	$V_{OUT}+0.3V \leq V_{IN} \leq 5V$		0.01	0.1	%/V
V_{BIAS} Line Regulation		$3.0V < V_{BIAS} < 5.5V$, ($V_{BIAS} > V_{OUT}+1.6$)		0.01	0.1	%/V
Ripple Rejection	$PSRR^{(3)}$	V_{IN} to V_{OUT} , $f=1kHz$, $V_{IN}=V_{OUT}+0.5V$, $V_{OUT}=1.05V$, Ripple 0.2Vp-p, $I_{OUT}=30mA$	60	75		dB
		V_{BIAS} to V_{OUT} , $f=1kHz$, $V_{IN}=V_{OUT}+0.5V$, $V_{OUT}=1.05V$, Ripple 0.2Vp-p, $I_{OUT}=30mA$	65	85		
Output Noise	$e_n^{(3)}$	$V_{IN}= V_{OUT}+0.5V$, $f= 10Hz$ to $100kHz$		30* V_{OUT}	60* V_{OUT}	μV_{RMS}
EN Pull-down Current	I_{EN}	$V_{EN}=5.5V$, $V_{BIAS}=5.5V$		0.3	1	μA
EN Input Voltage High	V_{ENH}		0.9			V
EN Input Voltage Low	V_{ENL}				0.4	V
Output Resistance of Auto Discharge at Off State	R_{DIS}	$V_{EN}=0V$, $V_{OUT}=0.5V$	80	150	220	Ω
Line Transient	$V_{TRLN}^{(3)}$	$V_{IN}= V_{OUT}+0.3$ to $V_{OUT}+1.3$ in 10us, $I_{OUT}=1mA$, $T_A=25^{\circ}C$		5	20	mV
		$V_{IN}= V_{OUT}+1.3$ to $V_{OUT}+0.3$ in 10us, $I_{OUT}=1mA$, $T_A=25^{\circ}C$		5	20	mV

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Electrical Characteristics(Continued)

(Unless otherwise noted , $V_{IN}=V_{OUT}+0.3V$, $V_{BIAS}= 3.0V$, $I_{OUT}=10mA$, $C_{IN}=10\mu F$, $C_{OUT}=22\mu F$, $C_{BIAS}=1\mu F$, $T_A = -40^{\circ}C \sim 125^{\circ}C$. Typical values are at. $T_A = 25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Load Transient	$V_{TRLD}^{(3)}$	$I_{OUT}=1mA$ to $1000mA$ in $10\mu s$ $V_{IN}= V_{OUT}+0.5V$, $T_A=25^{\circ}C$		130	200	mV
		$I_{OUT}=1000mA$ to $1mA$ in $10\mu s$ $V_{IN}= V_{OUT}+0.5V$, $T_A=25^{\circ}C$		70	130	mV
Turn-On Time	$T_{ON}^{(3)}$	$V_{OUT}=1.05V$, From assertion of V_{EN} to $V_{OUT}=90\%V_{OUT(NOM)}$	100	150	300	μs
Thermal Shutdown Threshold	$T_{TSD}^{(3)}$	T_J rising	140	160	175	$^{\circ}C$
Thermal Shutdown Hysteresis	$T_{HYS}^{(3)}$	T_J falling from shutdown	10	20	35	$^{\circ}C$
ESD	HBM	Reference: ESDA/JEDEC JS-001-2017	± 4000			V
	CDM	Reference: ESDA/JEDEC JS-002-2014	± 1500			V
Latch Up		Reference: JEDEC78	± 200			mA

Notes:

1: The maximum input voltage should take into account the maximum power consumption ($P_D(max)$). The calculation formula is as follows:

$$P_D(max) = (V_{IN(max)} - V_{OUT}) \times I_{OUT}$$

The maximum power consumption of the circuit is 1150mW.

$$V_{IN(max)}=1150mW / I_{OUT} + V_{OUT}$$

For example:

If $V_{OUT}= 1.05V$, $I_{OUT} =1000mA$, The maximum input voltage is $V_{IN(max)}=1150mW/1000mA+1.05=2.2V$

2: V_{DROP} FT test method: test the V_{OUT} voltage at $V_{SET}+V_{DROPMAX}$ with output current.

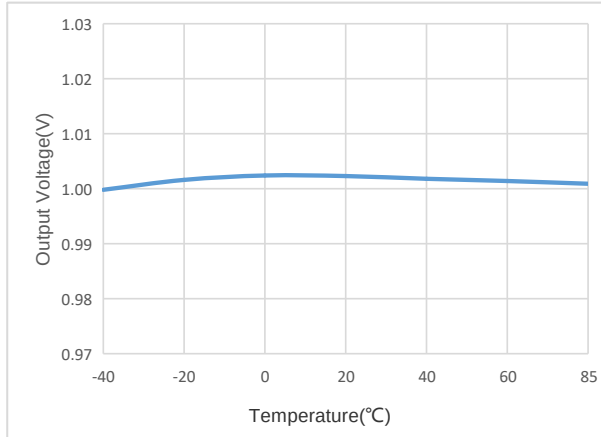
3: Guaranteed by design and characterization. not a FT item.

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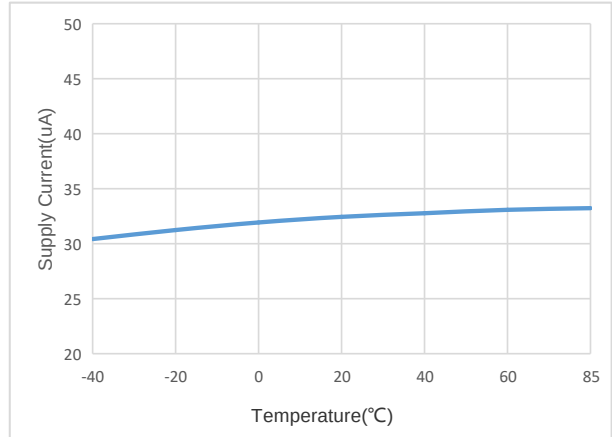
Typical Characteristics

Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.

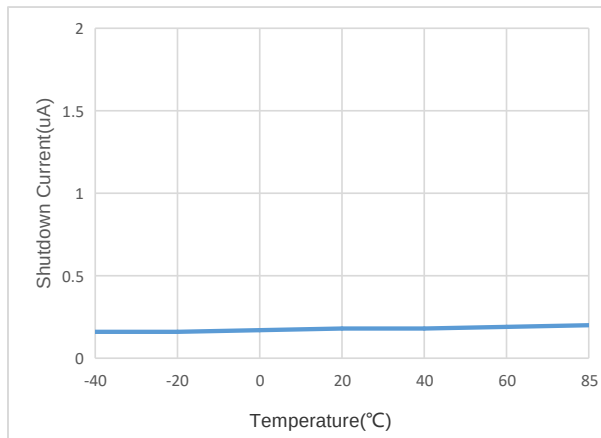
($V_{IN}=1.30V$, $V_{BIAS}=3.0V$, $I_{OUT}=1mA$, $C_{IN}=10\mu F$, $C_{OUT}=10\mu F$, $C_{BIAS}=1\mu F$, $V_{OUT}=1V$)



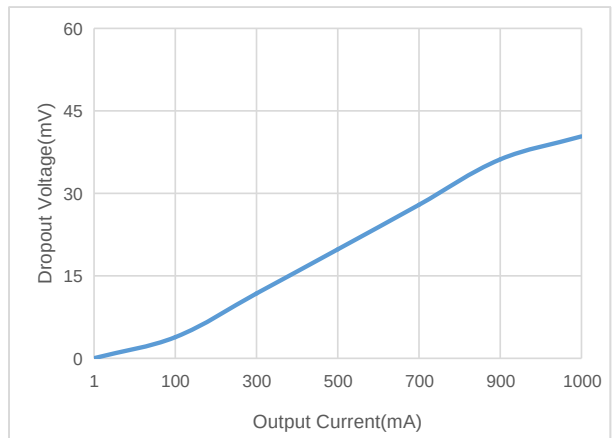
Output Voltage VS Temperature



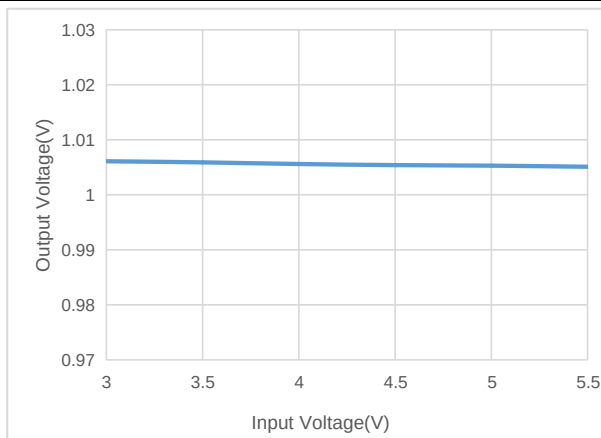
Supply Current VS Temperature



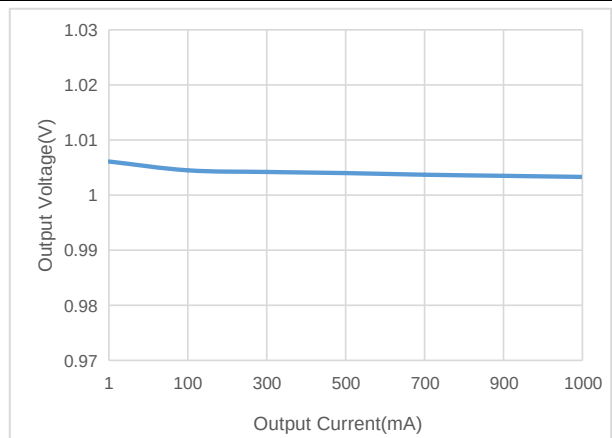
Shutdown Current VS Temperature



Dropout Voltage vs. Output Current



Output Voltage VS BIAS Input Voltage



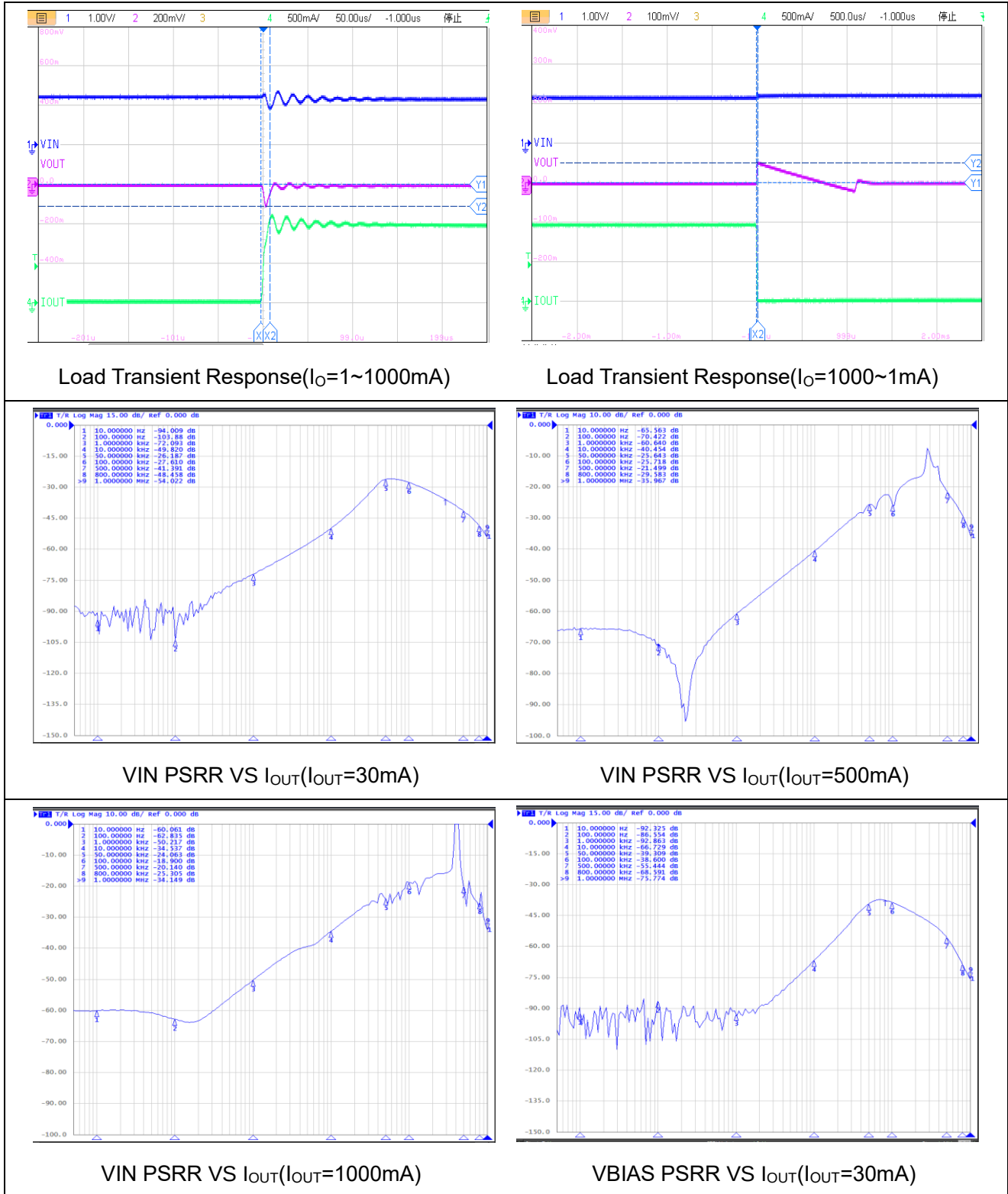
Output Voltage VS Output Current

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Typical Characteristics (Continued)

Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.

($V_{IN}=1.30V$, $V_{BIAS}=3.0V$, $I_{OUT}=1mA$, $C_{IN}=10\mu F$, $C_{OUT}=10\mu F$, $C_{BIAS}=1\mu F$, $V_{OUT}=1V$)

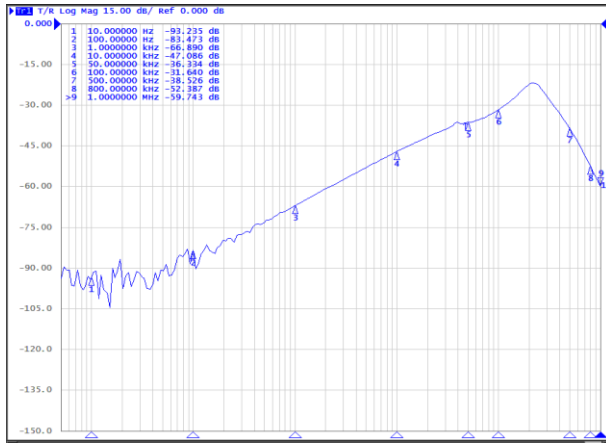


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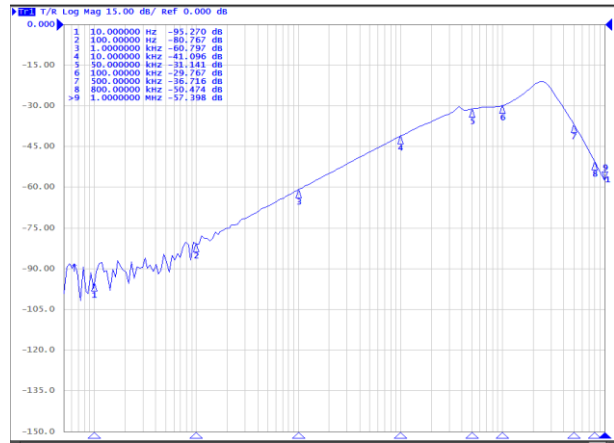
Typical Characteristics (Continued)

Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.

($V_{IN}=1.30V$, $V_{BIAS}= 3.0V$, $I_{OUT}=1mA$, $C_{IN}=10\mu F$, $C_{OUT}=10\mu F$, $C_{BIAS}=1\mu F$, $V_{OUT}=1V$)

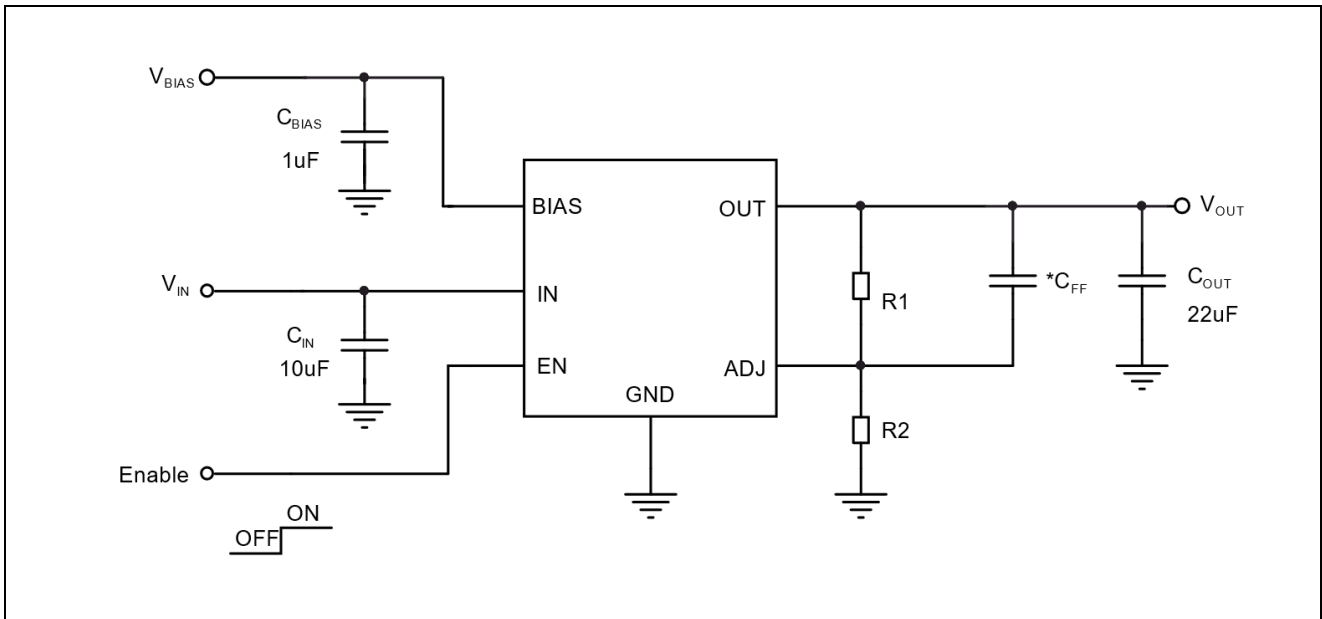


VBIAS PSRR VS I_{OUT} ($I_{OUT}=500mA$)



VBIAS PSRR VS I_{OUT} ($I_{OUT}=1000mA$)

Application Circuits

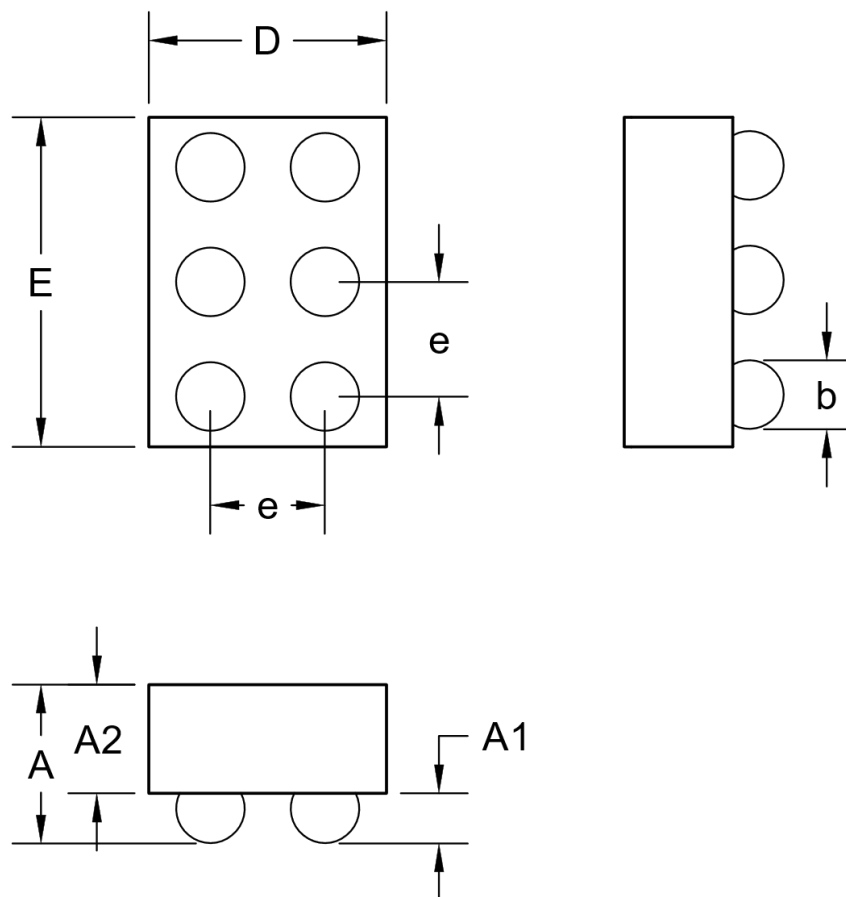


Note*: $V_{OUT} = 0.5 \times (1 + R1/R2)$, ($R1+R2$) no greater than 100k Ω . The feedforward capacitor C_{FF} is optional for the optimization of transient response, suggested value is 10nF.

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Package Dimension

WLCSP6

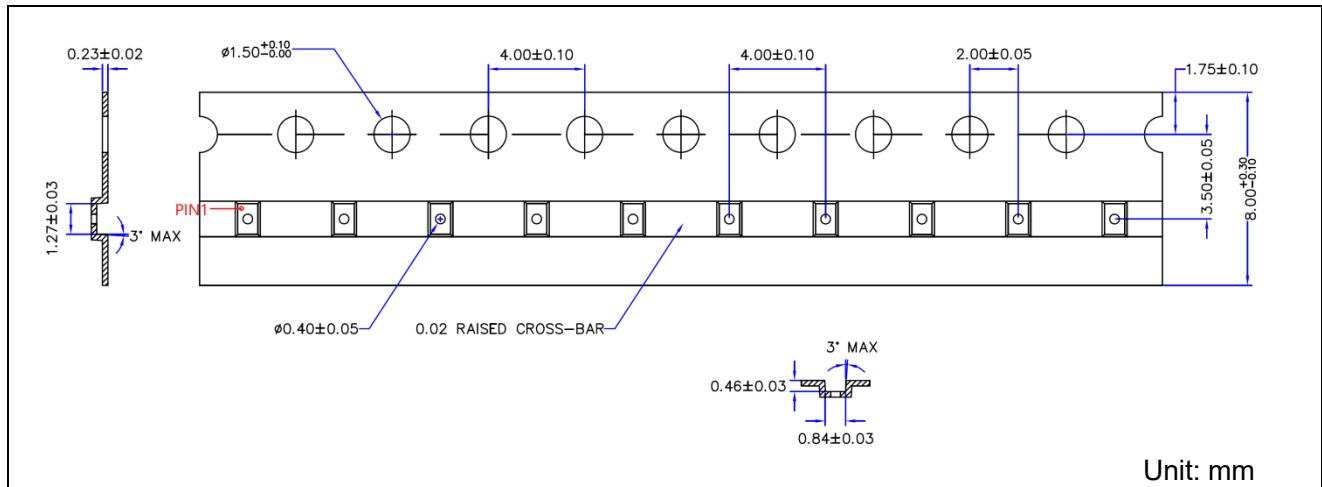


Dimensions Table (Units: mm)

Symbol	Min	Nom	Max
A	0.315	0.36	0.405
A1	0.04	0.06	0.08
A2	0.275	0.30	0.325
b	0.21	0.24	0.27
D	0.71	0.74	0.77
E	1.11	1.14	1.17
e	0.400 BSC		

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Tape Information



Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
1.0	2019-08-16	Initial Version	Liu Yi Guo	Liu Yi Guo	Zhu Jun Li
1.1	2019-09-08	Add Output Range and VBIAS Test Condition	Liu Yi Guo	Liu Yi Guo	Zhu Jun Li
1.2	2019-09-10	Add "Output Voltage Adjust" Describe and "Recommended Operating Conditions" . Add UVLO/PSRR min/max Value	Liu Yi Guo	Liu Yi Guo	Zhu Jun Li
1.3	2019-11-14	Update Output noise in EC table	Liu Yi Guo	Liu Yi Guo	Zhu Jun Li
1.4	2019-12-18	Update Package Dimension	Liu Yi Guo	Liu Yi Guo	Liu Jia Ying
1.5	2019-12-27	Update Application Circuit	Liu Yi Guo	Liu Yi Guo	Liu Jia Ying
1.6	2020-06-01	Update Package Dimension	Liu Yi Guo	Liu Yi Guo	Liu Jia Ying
1.7	2020-06-15	Add Tape Information	Liu Yi Guo	Liu Yi Guo	Liu Jia Ying
1.8	2020-06-28	Update Application Circuit	Liu Yi Guo	Liu Yi Guo	Liu Jia Ying
1.9	2020-08-21	Update Test Condition of I_{ON}	Liu Yi Guo	Liu Yi Guo	Liu Jia Ying
2.0	2021-1-6	Add Thermal Resistance, Junction-to-Air in AMR and Adjust the Format	Wuxj	Wuxj	Liu Jy
2.1	2023-3-28	Update Typeset	Shibo	Shibo	Liu Jy
2.2	2023-5-15	Add Typical Characteristic Graph	Tugz	Shib	Liu Jy